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PLENARY 5: Aida Todri-Sanial

Date: Wednesday, September 11, 2024
Room: Auditorium A
Chair(s): James Myers, *imec*

Computing with Physics – Theory, Devices and Circuit Design Perspective

Aida Todri-Sanial
Eindhoven University of Technology, Netherlands

Power & mmWave Devices

Date: Wednesday, September 11, 2024
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[1]Fraunhofer Institute for Photonic Microsystems IPMS, Germany; [2]Dresden University of Technology, Germany

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Date: Wednesday, September 11, 2024
Room: Auditorium B
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Date: Wednesday, September 11, 2024
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Date: Wednesday, September 11, 2024
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Date: Wednesday, September 11, 2024
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[1]Katholieke Universiteit Leuven, Belgium; [2]Interuniversity Micro Electronics Center IMEC, Belgium

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Date: Wednesday, September 11, 2024
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Date: Wednesday, September 11, 2024
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[1]Peking University, China; [2]Advanced Institute of Information Technology, Peking University, China

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Cellular & IoT Subsystems

Date: Wednesday, September 11, 2024
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[1]University of Washington, United States; [2]Boeing Company, United States; [3]Creonex Systems Inc., United States

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Date: Wednesday, September 11, 2024
Room: Auditorium A
Chair(s): Mikael Östling, *KTH*
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[1]STMicroelectronics, France; [2]Université Grenoble Alpes, CEA-Leti, France;
[3]IEMN, University of Lille, CNRS, École Centrale de Lille, France

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[1]Stanford University, United States; [2]University of Southern California, United States

Cryo-CMOS Circuits for Trapped-Ion Quantum Computer

Date: Wednesday, September 11, 2024
Room: Room 1+2
Chair(s): Lotte Geck, *Jülich*
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Date: Wednesday, September 11, 2024
Room: Room 12
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[3]National University of Science and Technology POLITEHNICA Bucharest, Romania

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Date: Thursday, September 12, 2024
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Date: Thursday, September 12, 2024
Room: Room 1+2
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Date: Thursday, September 12, 2024
Room: Room 4+5
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Date: Thursday, September 12, 2024
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Date: Thursday, September 12, 2024
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Date: Thursday, September 12, 2024
Room: Room 1+2
Chair(s): Luca Bertulessi, *Politecnico di Milano*
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Date: Thursday, September 12, 2024
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Date: Thursday, September 12, 2024
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Compact Modeling

Date: Thursday, September 12, 2024
Room: Room 12
Chair(s): Benjamin Iñiguez, *University Rovira i Virgili*
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Compact Model of Conductive-Metal-Oxide/HfO_x Analog Filamentary ReRAM Devices 749
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